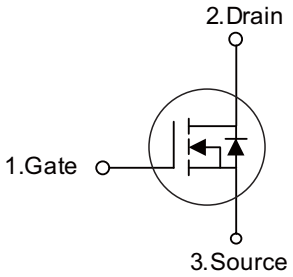
## ■ PRODUCT CHARACTERISTICS

| | |
|---|---|
| VDSS | 650V |
| $R_{DS}$(on)max(@$V_{GS}$ =10 V) | 2.2Ω |
| Qg@type | 25nC |
| ID | 5A |

## Symbol

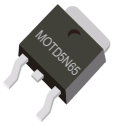



## ■ APPLICATIONS

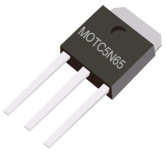
* High frequency switching mode power supply
* Electronic ballast
* LED power supplies

## ■ FEATURES

* $R_{DS(ON)}$ ≤ 2.2Ω @ $V_{GS}$=10V
* High Switching Speed




TO-252




TO-251

## ■ ORDER INFORMATION

| Order codes | | Package | Packing |
|---|---|---|---|
| Halogen-Free | Halogen | | |
| N/A | MOT5N65D | TO-252 | 2500 pieces /Reel |
| N/A | MOT5N65C | TO-251 | 70 pieces/Tube |

## ■ ABSOLUTE MAXIMUM RATINGS ($T_C$ = 25°C, unless otherwise specified)

| PARAMETER | | SYMBOL | RATINGS | UNIT |
|---|---|---|---|---|
| Drain-Source Voltage | | $V_{DSS}$ | 650 | V |
| Gate-Source Voltage | | $V_{GSS}$ | ±30 | V |
| Drain Current | Continuous | $I_D$ | 5 | A |
| | Pulsed (Note 2) | $I_{DM}$ | 10 | A |
| Avalanche Energy | Single Pulsed (Note 3) | $E_{AS}$ | 112 | mJ |
| Peak Diode Recovery dv/dt (Note 4) | | dv/dt | 3.2 | V/ns |
| Power Dissipation | TO-251/252 | $P_D$ | 54 | W |
| Junction Temperature | | $T_J$ | +150 | °C |
| Storage Temperature | | $T_{STG}$ | -55 ~ +150 | °C |

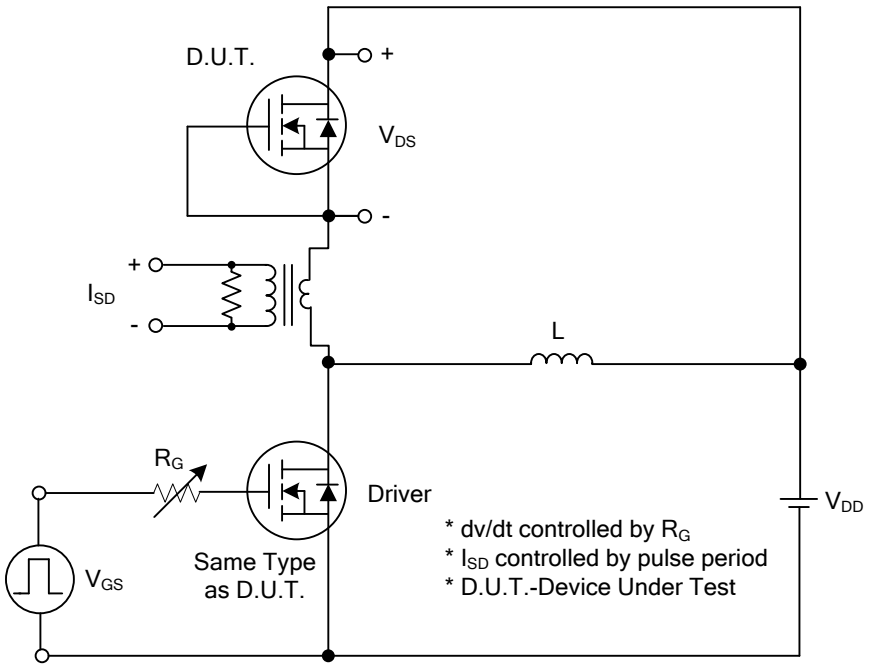
Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.
2. Repetitive Rating: Pulse width limited by maximum junction temperature.
3. L = 10mH, $I_{AS}$ = 4.73A, $V_{DD}$ = 50V, $R_G$ = 25 Ω Starting $T_J$ = 25°C
4. $I_{SD}$ ≤ 7.0A, di/dt ≤200A/μs, $V_{DD}$ ≤$BV_{DSS}$, Starting $T_J$ = 25°C

■ ELECTRICAL CHARACTERISTICS ($T_C$ = 25°C, unless otherwise specified)

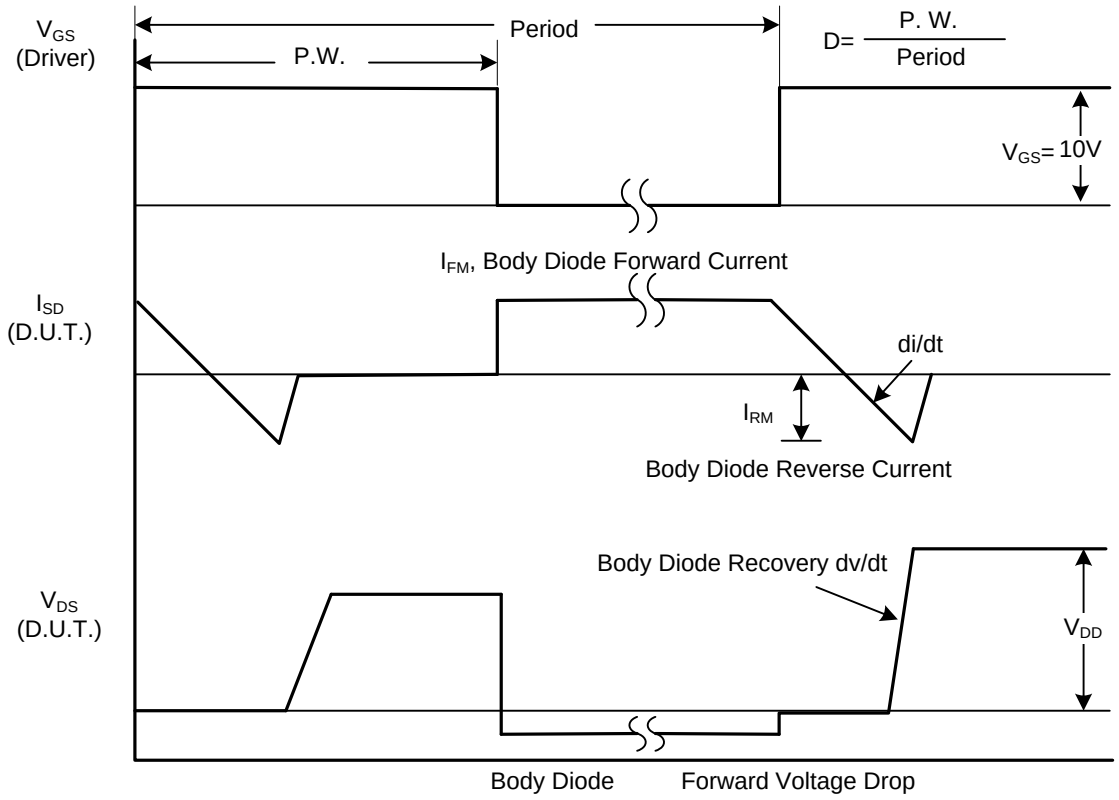
| PARAMETER | | SYMBOL | TEST CONDITIONS | MIN | TYP | MAX | UNIT |
|---|---|---|---|---|---|---|---|
| **OFF CHARACTERISTICS** | | | | | | | |
| Drain-Source Breakdown Voltage | | $BV_{DSS}$ | $V_{GS}$=0V, $I_D$= 250μA | 650 | | | V |
| Drain-Source Leakage Current | | $I_{DSS}$ | $V_{DS}$=650V, $V_{GS}$=0V | | | 10 | μA |
| Gate-Source Leakage Current | Forward | $I_{GSS}$ | $V_{GS}$=30V, $V_{DS}$=0V | | | 100 | nA |
| | Reverse | | $V_{GS}$=-30V, $V_{DS}$=0V | | | -100 | nA |
| **ON CHARACTERISTICS** | | | | | | | |
| Gate Threshold Voltage | | $V_{GS(TH)}$ | $V_{DS}$=$V_{GS}$, $I_D$=250μA | 2.0 | | 4.0 | V |
| Static Drain-Source On-State Resistance | | $R_{DS(ON)}$ | $V_{GS}$=10V, $I_D$=2.5A | | 1.92 | 2.2 | Ω |
| **DYNAMIC CHARACTERISTICS** | | | | | | | |
| Input Capacitance | | $C_{ISS}$ | $V_{GS}$=0V, $V_{DS}$=25V, f=1.0 MHz | | 623 | | pF |
| Output Capacitance | | $C_{OSS}$ | | | 62 | | pF |
| Reverse Transfer Capacitance | | $C_{RSS}$ | | | 2.9 | | pF |
| **SWITCHING CHARACTERISTICS** | | | | | | | |
| Total Gate Charge (Note 1) | | $Q_G$ | $V_{DS}$=100V, $V_{GS}$=10V, $I_D$=2.0A $I_G$=1mA (Note 1, 2) | | 15 | | nC |
| Gateource Charge | | $Q_{GS}$ | | | 5.6 | | nC |
| Gate-Drain Charge | | $Q_{GD}$ | | | 2.5 | | nC |
| Turn-on Delay Time (Note 1) | | $t_{D(ON)}$ | $V_{DS}$=30V, $V_{GS}$=10V, $I_D$=0.5A, $R_G$=25Ω (Note 1, 2) | | 4.4 | | ns |
| Rise Time | | $t_R$ | | | 24 | | ns |
| Turn-off Delay Time | | $t_{D(OFF)}$ | | | 122 | | ns |
| Fall-Time | | $t_F$ | | | 25 | | ns |
| **SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS** | | | | | | | |
| Maximum Body-Diode Continuous Current | | $I_S$ | | | | 5 | A |
| Maximum Body-Diode Pulsed Current | | $I_{SM}$ | | | | 10 | A |
| Drain-Source Diode Forward Voltage (Note 1) | | $V_{SD}$ | $V_{GS}$=0V, $I_S$=5.0A | | | 1.4 | V |
| Reverse Recovery Time (Note 1) | | $t_{rr}$ | $V_{GS}$=0V, $I_S$=5.0A, $dI_F/dt$=100A/μs (Note1) | | 328 | | ns |
| Reverse Recovery Charge | | $Q_{rr}$ | | | 2.65 | | μC |

Notes: 1. Pulse Test : Pulse width ≤ 300μs, Duty cycle ≤ 2%.
2. Essentially independent of operating temperature.

■ TEST CIRCUITS AND WAVEFORMS

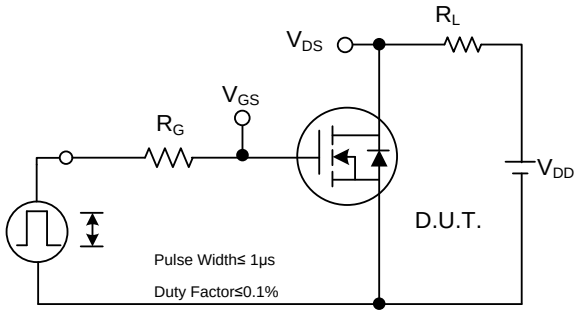



**Peak Diode Recovery dv/dt Test Circuit**

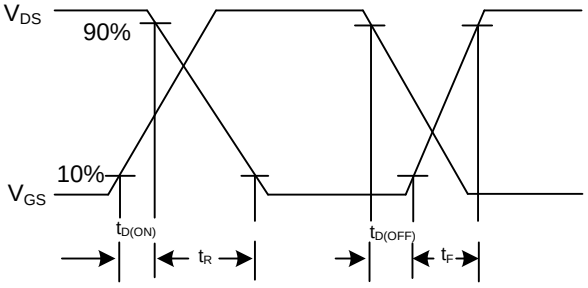



**Peak Diode Recovery dv/dt Waveforms**

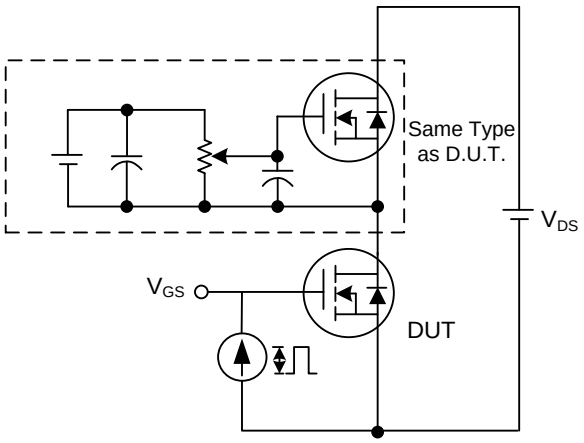
■ TEST CIRCUITS AND WAVEFORMS(Cont.)



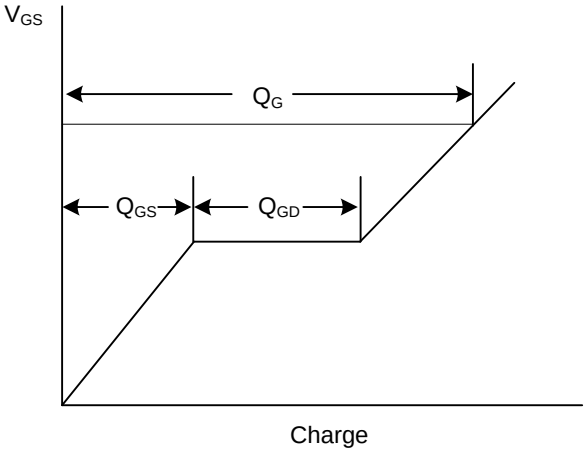

**Switching Test Circuit**



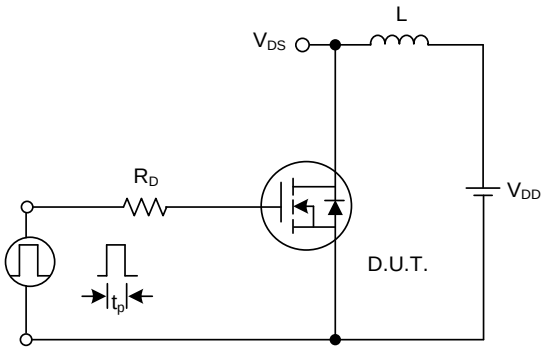

**Switching Waveforms**



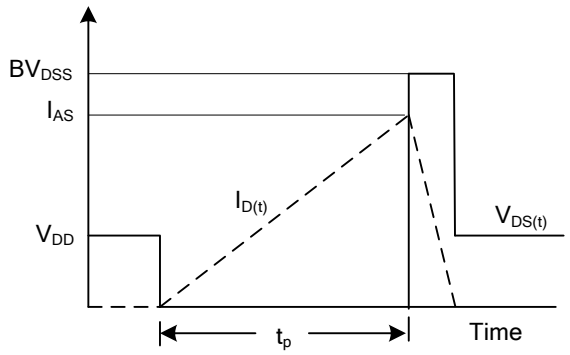

**Gate Charge Test Circuit**




**Gate Charge Waveform**



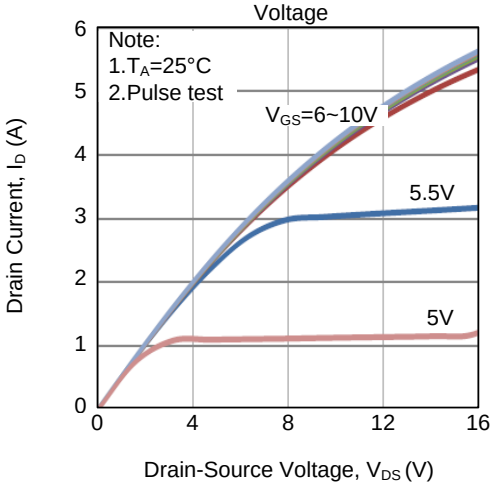

**Unclamped Inductive Switching Test Circuit**



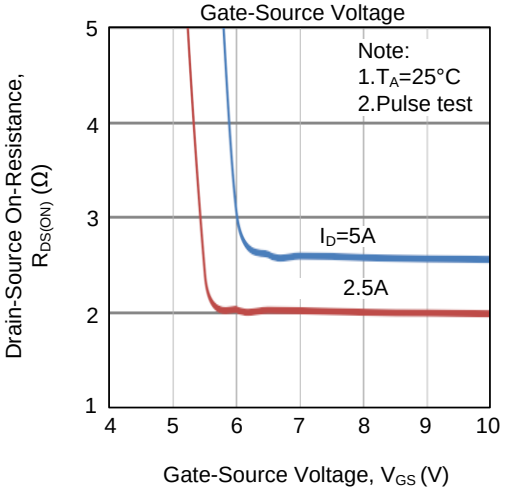

**Unclamped Inductive Switching Waveforms**

## ■ TYPICAL CHARACTERISTICS

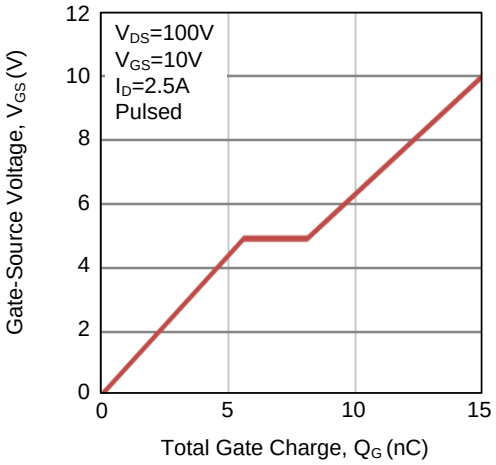
Drain Current vs. Drain-Source Voltage



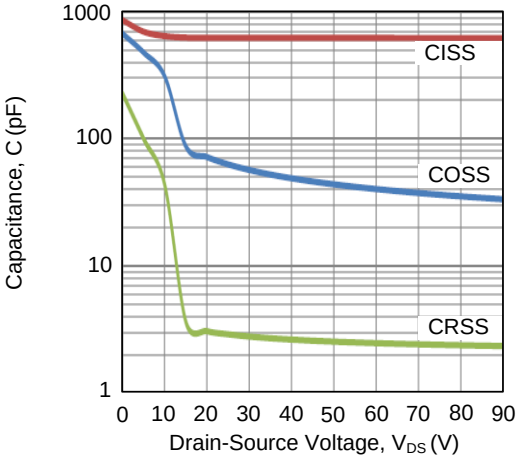

Drain-Source On-Resistance vs. Gate-Source Voltage



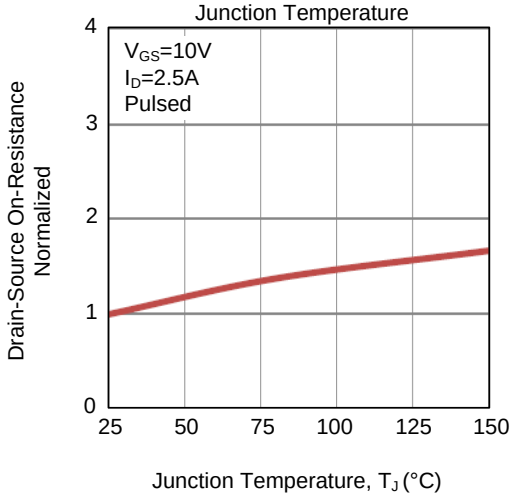

Gate Charge Characteristics



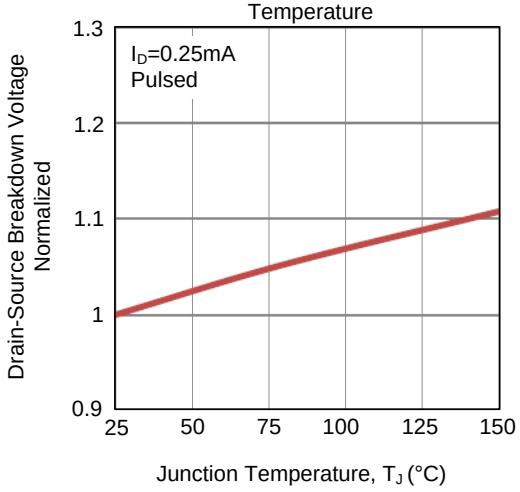

Capacitance Characteristics




Drain-Source On-Resistance vs. Junction Temperature

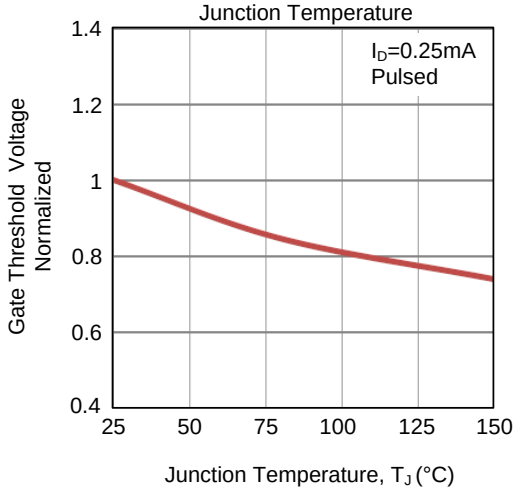



Breakdown Voltage vs. Junction Temperature

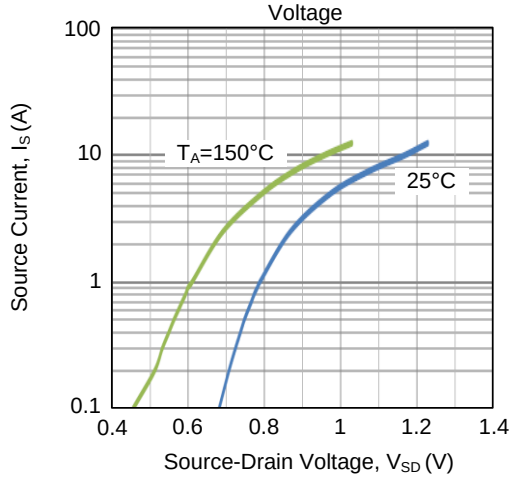


## ■ TYPICAL CHARACTERISTICS(Cont.)

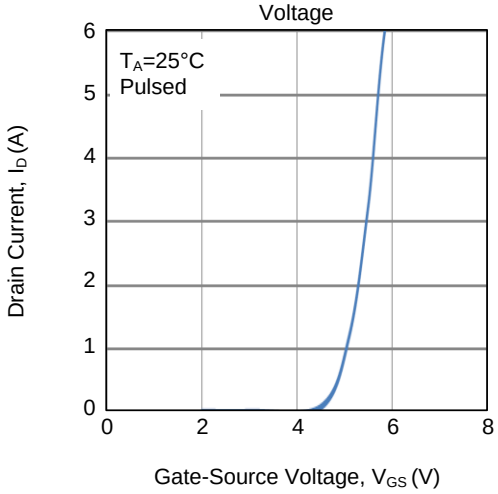
Gate Threshold Voltage vs. Junction Temperature



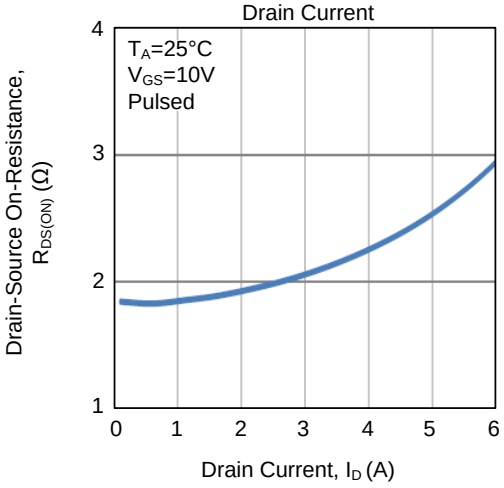

Source Current vs. Source-Drain Voltage



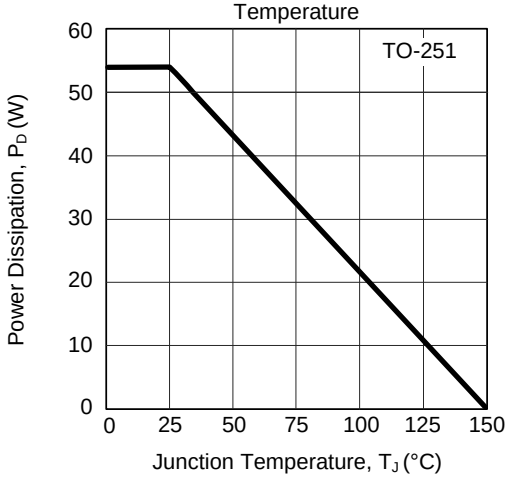

Drain Current vs. Gate-Source Voltage



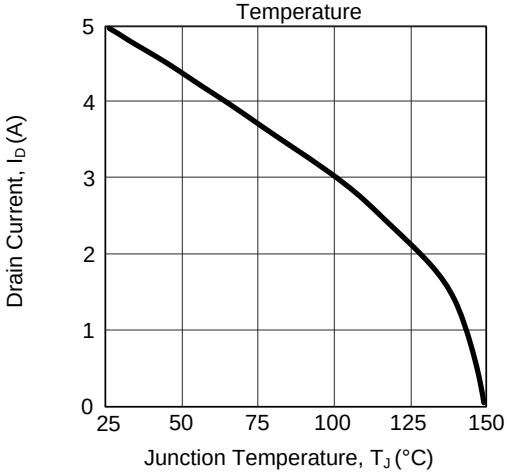

Drain-Source On-Resistance vs. Drain Current



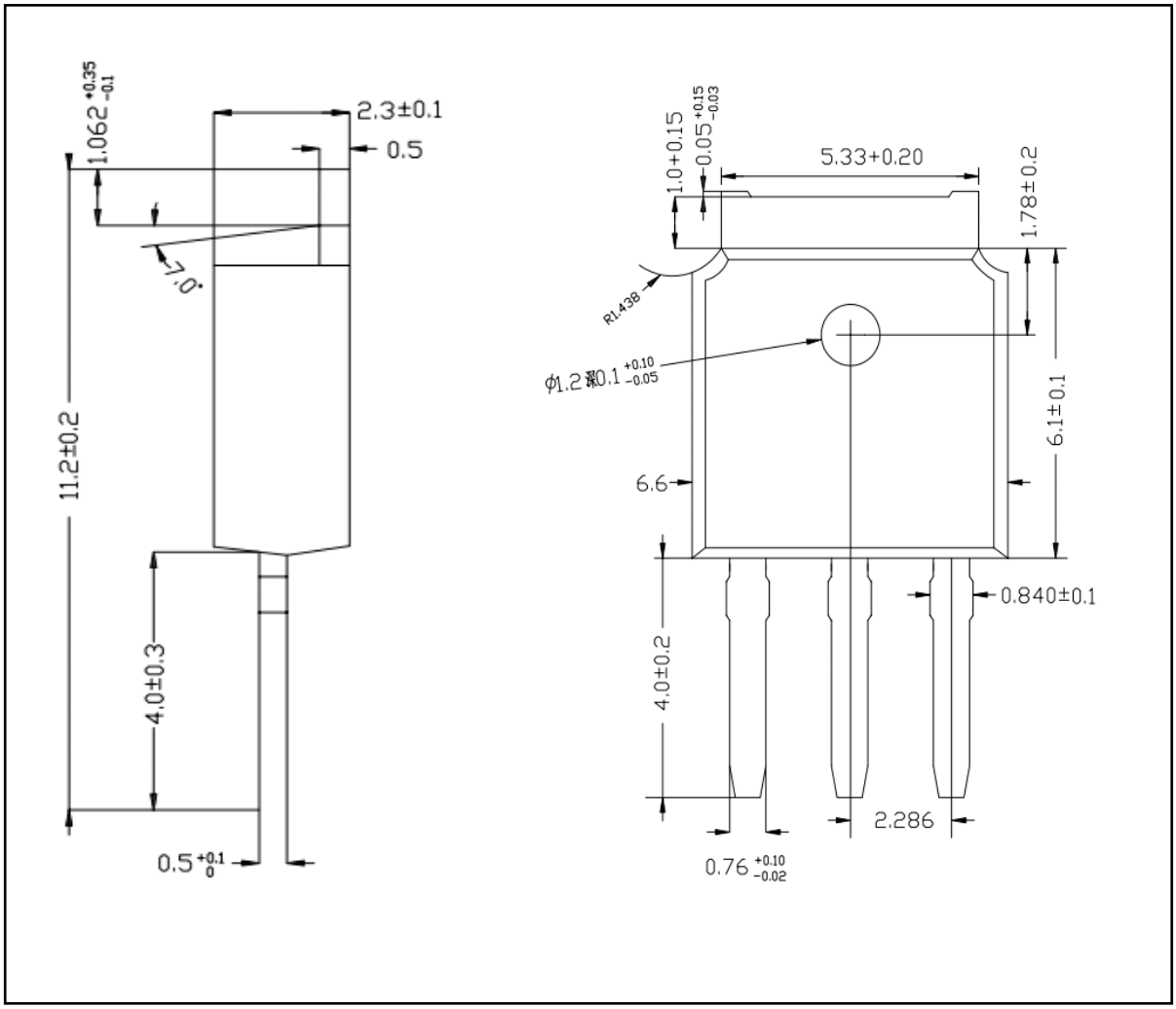

Power Dissipation vs. Junction Temperature




Drain Current vs. Junction Temperature



■ TO-251-3L PACKAGE OUTLINE DIMENSIONS



■ TO-252-2L PACKAGE OUTLINE DIMENSIONS